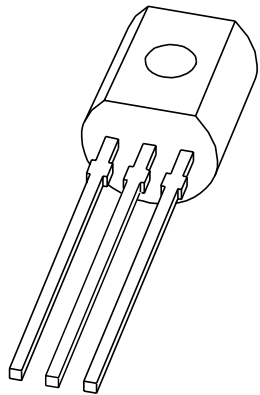


DATA SHEET



2N4401 NPN switching transistor

Product specification
Supersedes data of 1999 Apr 23

2004 Oct 28

NPN switching transistor

2N4401

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

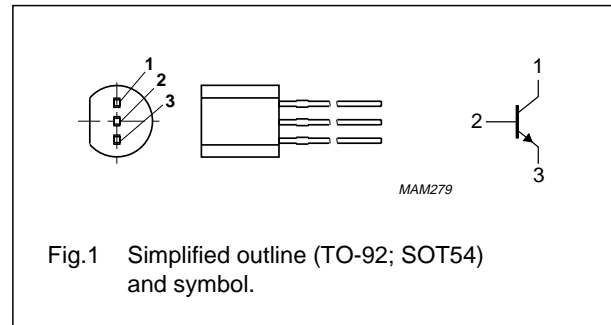
- Industrial and consumer switching applications.

DESCRIPTION

NPN switching transistor in a TO-92; SOT54 plastic package. PNP complement: 2N4403.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
2N4401	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	60	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	600	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	630	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	200	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

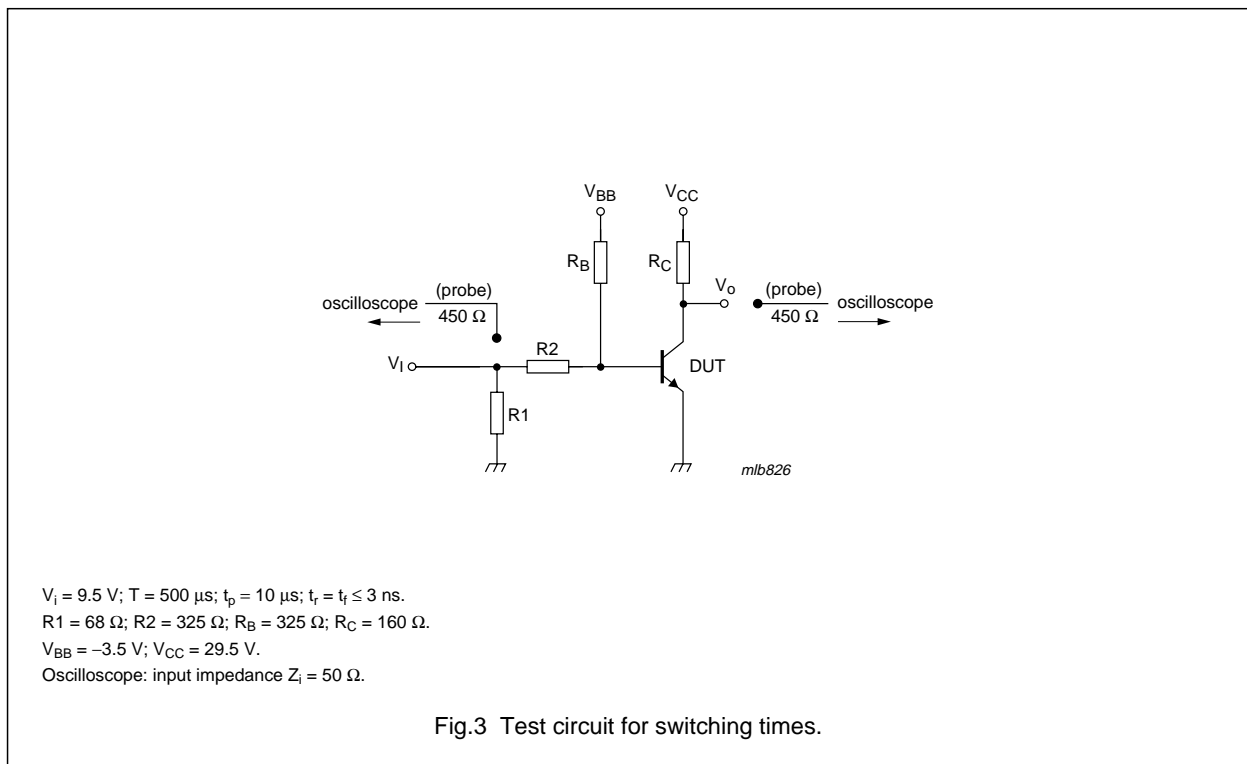
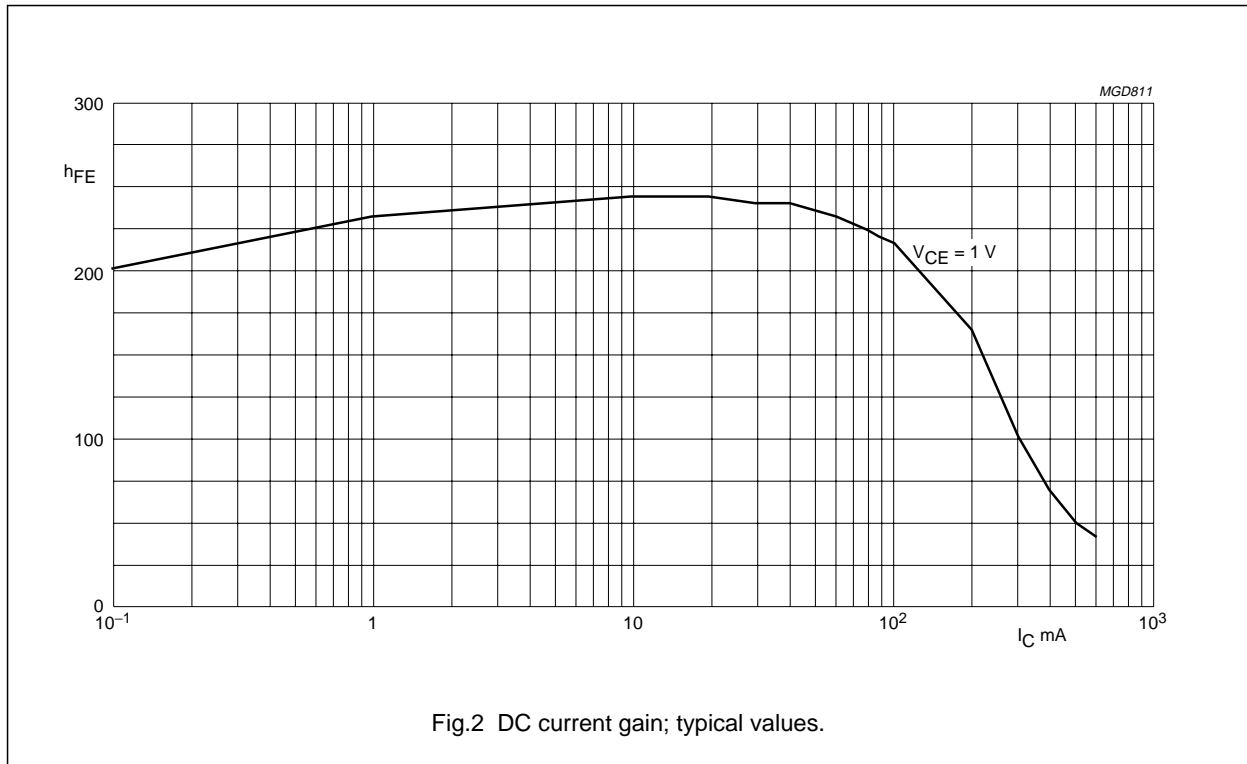
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 60\text{ V}; I_E = 0\text{ A}$	–	50	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 6\text{ V}; I_C = 0\text{ A}$	–	50	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$; see Fig.2 $I_C = 0.1\text{ mA}$	20	–	
		$I_C = 1\text{ mA}$	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$; note 1	–	400	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1	–	750	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$; note 1	–	950	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1	–	1.2	V
C_c	collector capacitance	$V_{CB} = 5\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	–	6.5	pF
C_e	emitter capacitance	$V_{EB} = 500\text{ mV}; I_C = I_E = 0\text{ A}; f = 1\text{ MHz}$	–	30	pF
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 20\text{ mA}; f = 100\text{ MHz}$	250	–	MHz
Switching times (between 10 % and 90 % levels); see Fig.3					
t_{on}	turn-on time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA}; I_{Boff} = -15\text{ mA}$	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

NPN switching transistor

2N4401



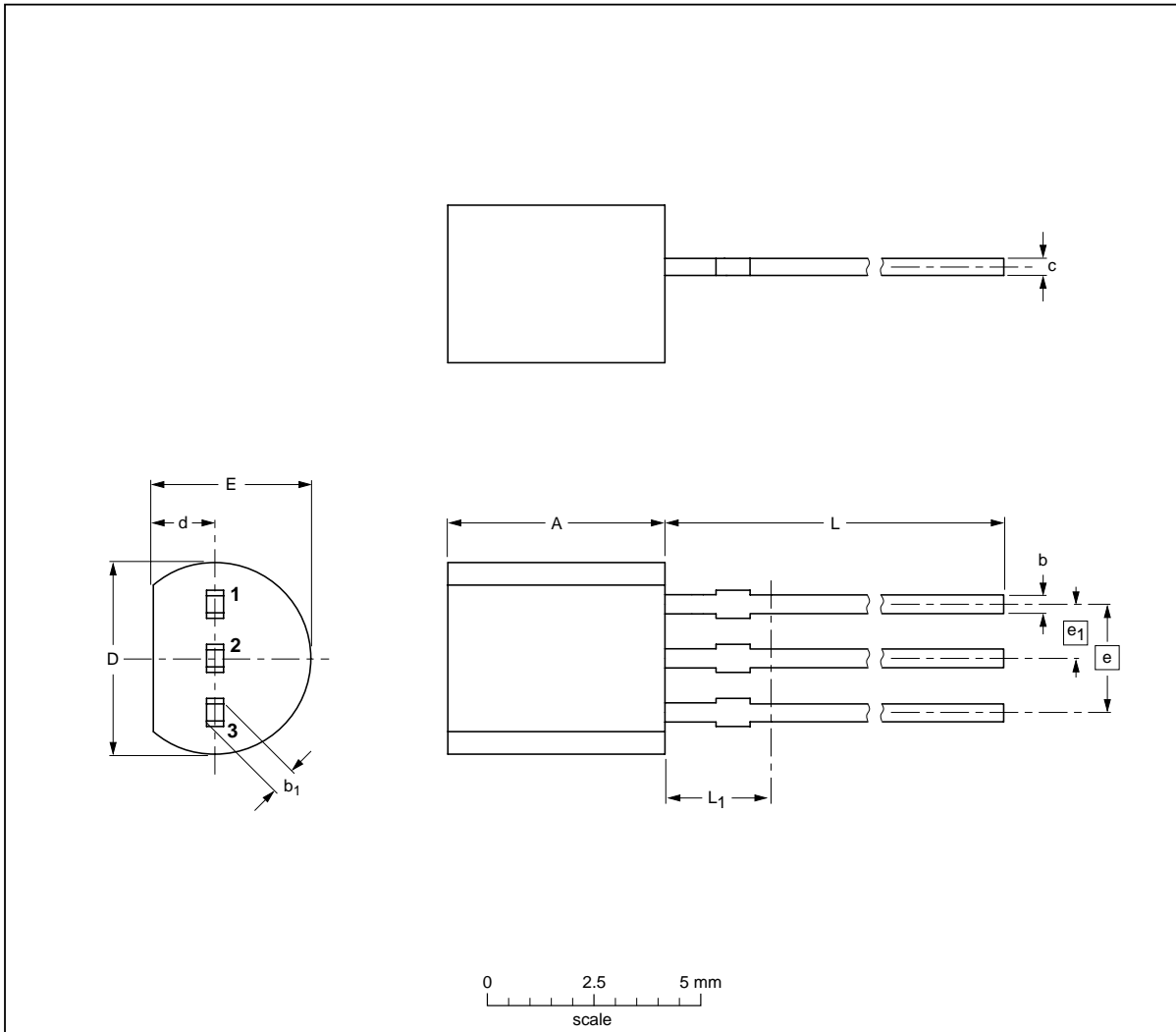
NPN switching transistor

2N4401

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		-97-02-28- 04-06-28

NPN switching transistor

2N4401

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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